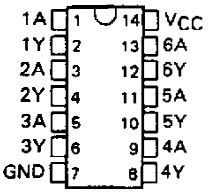
SDLS138

SN74LS19A, SN74LS24A
SCHMITT-TRIGGER POSITIVE-NAND GATES AND INVERTERS WITH TOTEM-POLE OUTPUTS

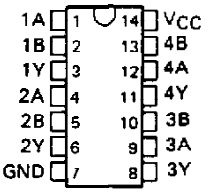
JANUARY 1981 – REVISED MARCH 1988

- Functionally and Mechanically Identical to 'LS13, 'LS14, and 'LS132, Respectively
- Improved Line-Receiving Characteristics
- P-N-P Inputs Reduce System Loading
- Excellent Noise Immunity with Typical Hysteresis of 0.8 V

SN74LS19A . . . D, J, OR N PACKAGE
(TOP VIEW)



SN74LS24A . . . D, J, OR N PACKAGE
(TOP VIEW)



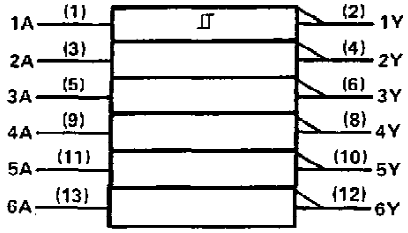
description

Each circuit functions as a NAND gate or inverter, but because of the Schmitt action, it has different input threshold levels for positive-going (V_{T+}) and for negative-going (V_{T-}) signals. The hysteresis or backlash, which is the difference between the two threshold levels ($V_{T+} - V_{T-}$), is typically 800 millivolts.

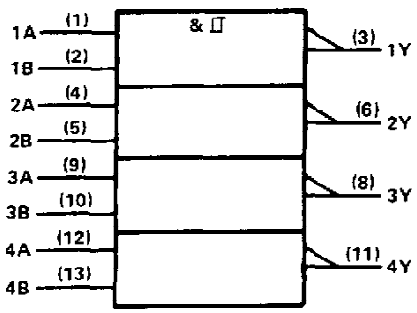
These circuits are temperature-compensated and can be triggered from the slowest of input ramps and still give clean, jitter-free output signals.

logic symbols†

SN74LS19A



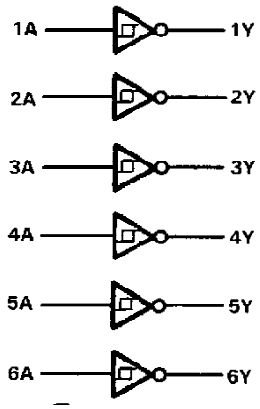
SN74LS24A



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

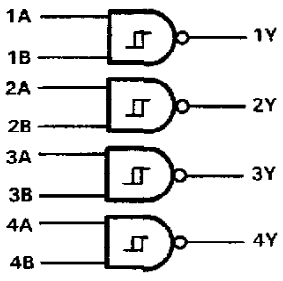
logic diagrams (positive logic)

SN74LS19A



$Y = \overline{A}$

SN74LS24A



$Y = \overline{AB}$

TEXAS INSTRUMENTS
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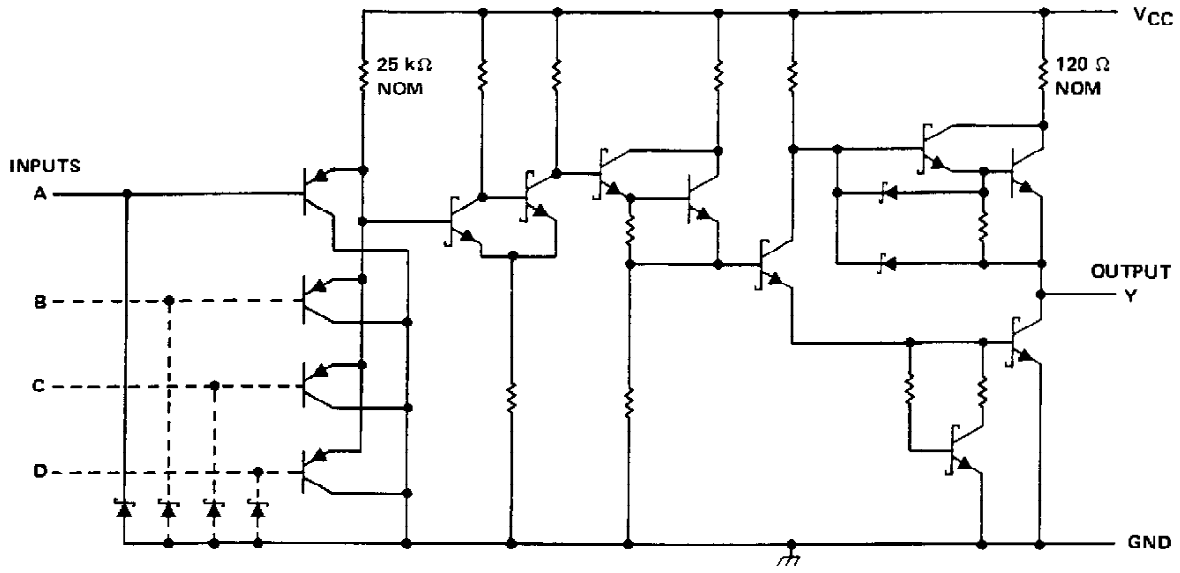
schematic (each gate)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (see Note 1) . . . . . 7 V
Input voltage . . . . . 7 V
Operating free-air temperature range . . . . . 0°C to 70°C
Storage temperature range . . . . . −65°C to 150°C

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}	4.75	5	5.25	V
High-level output current, I_{OH}			−400	μA
Low-level output current, I_{OL}			8	mA
Operating free-air temperature, T_A	0		70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			MIN	TYP‡	MAX	UNIT
V_{T+}	V_{CC} = 5 V			1.65	1.9	2.15	V
V_{T-}	V_{CC} = 5 V			0.75	1.0	1.25	V
Hysteresis ($V_{T+} - V_{T-}$)	V_{CC} = 5 V			0.4	0.9		V
V_{IK}	V_{CC} = MIN,	I_I = −18 mA			−1.5		V
V_{OH}	V_{CC} = MIN,	$V_I = V_{T-min}$	I_{OH} = −0.4 mA	2.7	3.4		V
V_{OL}	V_{CC} = MIN,	$V_I = V_{T+max}$	I_{OL} = 4 mA		0.25	0.4	V
			I_{OL} = 8 mA		0.35	0.5	
I_{T+}	V_{CC} = 5 V,	$V_I = V_{T+}$			−2	−20	μA
I_{T-}	V_{CC} = 5 V,	$V_I = V_{T-}$			−5	−30	μA
I_I	V_{CC} = MAX,	V_I = 7 V			0.1		mA
I_{IH}	V_{CC} = MAX,	V_I = 2.7 V				20	μA
I_{IL}	V_{CC} = MAX,	V_I = 0.4 V				−50	μA
I_{OS}§	V_{CC} = MAX,	$V_I = V_O$ = 0 V		−20		−100	mA
I_{CCH}	V_{CC} = MAX,	V_I = 0 V	'LS19A		9.9	18	mA
			'LS24A		6.6	12	
I_{CCL}	V_{CC} = MAX,	V_I = 4.5 V	'LS19A		17	30	mA
			'LS24A		11	20	

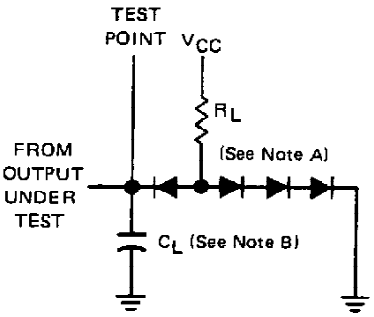
† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡ All typical values are at V_{CC} = 5 V, T_A = 25°C.
§ Not more than one output should be shorted at a time, and the duration of the short-circuit should not exceed one second.

switching characteristics, V_{CC} = 5 V, T_A = 25°C (see Figure 1)

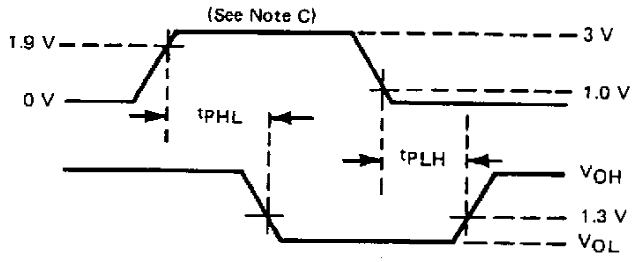
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN74LS19A			SN74LS24A			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Any	Y	R_L = 2 kΩ, C_L = 15 pF		13	20		13	20	ns
t_{PHL}	Any	Y			18	30		25	40	ns

t_{PLH} = Propagation delay time, low-to-high-level output
t_{PHL} = Propagation delay time, high-to-low-level output

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. All diodes are IN3064 or equivalent.
B. C_L includes probe and circuit capacitance.
C. The generator characteristics are: PRR = 1 MHz, t_r = 15 ns, t_p = 6 ns, Z_o = 50 Ω.

FIGURE 1

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